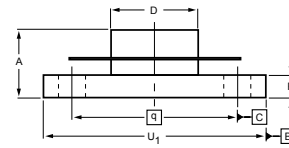


DESCRIPTION

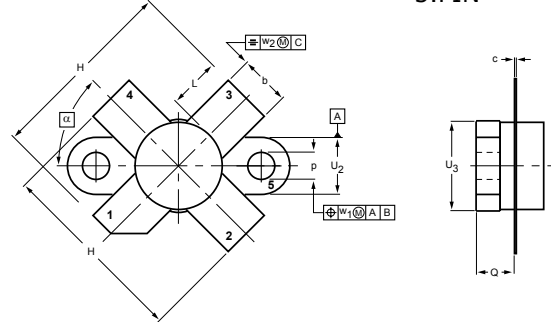
Designed for high gain amplifier applications up to 30 MHz

FEATURES

- Specified 28V, 30MHz Characteristic
- $P_o = 25W$
- $G_p = 22$ dB min. at 25 W/30 MHz
- Omnigold™ Metalization System



1. Collector
2. EMITTER
3. BASE
4. EMITTER
5. FIN



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.47 6.37	5.82 5.56	0.18 0.10	9.73 9.47	9.63 9.42	2.72 2.31	20.71 19.93	5.61 5.16	3.33 3.04	4.63 4.11	18.42	25.15 24.38	6.61 6.09	9.78 9.39	0.51	1.02	45°
inches	0.294 0.251	0.229 0.219	0.007 0.004	0.383 0.373	0.397 0.371	0.107 0.091	0.815 0.785	0.221 0.203	0.131 0.120	0.182 0.162	0.725	0.99 0.96	0.26 0.24	0.385 0.370	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	65	V
Collector-Emitter Voltage	V_{CES}	65	V
Collector-Emitter Voltage	V_{CEO}	35	V
Collector Current	I_C	3	A
Emitter-Base Voltage	V_{EBO}	4	V
Collector Power Dissipation	P_{DISS}	70	W
Junction Temperature	T_J	-65 to 175	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=50mA, V_{EB}=0$	65	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10mA, I_C=0$	4	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB}=30V, I_E=0$			1	mA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=1A$	10	35	-	
Collector Output Capacitance	C_{ob}	$V_{CB}=30V, I_E=0, f=1MHz$	-	60	80	pF
Power Gain	G_p	$V_{CC}=28V, P_{OUT}=25W, f=30MHz$	22	25	-	dB
Collector Efficiency	η_C		35	-	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.